

General Purpose Transistors

NPN Silicon

- We declare that the material of product compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

MMBT2222LT1
MMBT2222ALT1
S-MMBT2222LT1
S-MMBT2222ALT1

MAXIMUM RATINGS

Rating	Symbol	2222	2222A	Unit
Collector-Emitter Voltage	V_{CEO}	30	40	Vdc
Collector-Base Voltage	V_{CBO}	60	75	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	6.0	Vdc
Collector Current — Continuous	I_C	600	600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR- 5 Board, (1)	P_D	225	mW
$T_A = 25^\circ C$			
Derate above $25^\circ C$		1.8	$mW/^\circ C$
Thermal Resistance, Junction to Ambient	R_{JJA}	556	$^\circ C/W$
Total Device Dissipation	P_D	300	mW
Alumina Substrate, (2) $T_A = 25^\circ C$			
Derate above $25^\circ C$		2.4	$mW/^\circ C$
Thermal Resistance, Junction to Ambient	R_{JJA}	417	$^\circ C/W$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ C$

DEVICE MARKING

MMBT2222LT1 = M1B; MMBT2222ALT1 = 1P

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ C$ unless otherwise noted.)

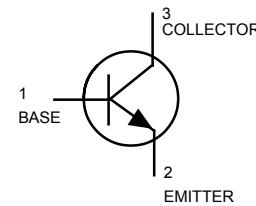
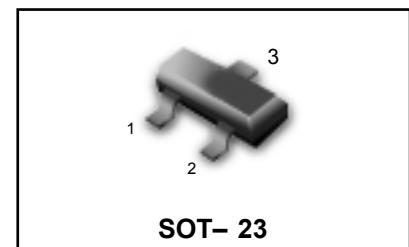
Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = 10 \mu A$, $I_B = 0$)	MMBT2222 MMBT2222A	$V_{(BR)CEO}$	30 40	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10 \mu A$, $I_E = 0$)	MMBT2222 MMBT2222A	$V_{(BR)CBO}$	60 75	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10 \mu A$, $I_C = 0$)	MMBT2222 MMBT2222A	$V_{(BR)EBO}$	5.0 6.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 60$ Vdc, $I_{EB(off)} = 3.0$ Vdc)	MMBT2222A	I_{CEX}	—	10	nAdc
Collector Cutoff Current ($V_{CB} = 50$ Vdc, $I_E = 0$)	MMBT2222	I_{CBO}	—	0.01	μAdc
($V_{CB} = 60$ Vdc, $I_E = 0$)	MMBT2222A		—	0.01	
($V_{CB} = 50$ Vdc, $I_E = 0, T_A = 125^\circ C$)	MMBT2222		—	10	
($V_{CB} = 60$ Vdc, $I_E = 0, T_A = 125^\circ C$)	MMBT2222A		—	10	
Emitter Cutoff Current ($V_{EB} = 3.0$ Vdc, $I_C = 0$)	MMBT2222A	I_{EBO}	—	100	nAdc
Base Cutoff Current ($V_{CE} = 60$ Vdc, $V_{EB(off)} = 3.0$ Vdc)	MMBT2222A	I_{BL}	—	20	nAdc

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



ORDERING INFORMATION

Device	Marking	Shipping
MMBT2222LT1	M1B	3000/Tape & Reel
S-MMBT2222LT1	M1B	3000/Tape & Reel
MMBT2222LT3	M1B	10000/Tape & Reel
S-MMBT2222LT3	M1B	10000/Tape & Reel
MMBT2222ALT1	1P	3000/Tape & Reel
S-MMBT2222ALT1	1P	3000/Tape & Reel
MMBT2222ALT3	1P	10000/Tape & Reel
S-MMBT2222ALT3	1P	10000/Tape & Reel

MMBT2222LT1 MMBT2222ALT1
S-MMBT2222LT1 S-MMBT2222ALT1
ELECTRICAL CHARACTERISTICS (T A = 25°C unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS				
DC Current Gain (I C = 0.1 mAdc, V CE = 10 Vdc)	h_{FE}	—	—	—
(I C = 1.0 mAdc, V CE = 10 Vdc)		35	—	—
(I C = 10 mAdc, V CE = 10 Vdc)		50	—	—
(I C = 10 mAdc, V CE = 10 Vdc, T A = -55°C)	MMBT2222A only	75	—	—
(I C = 150 mAdc, V CE = 10 Vdc) (3)		35	—	—
(I C = 150 mAdc, V CE = 1.0 Vdc) (3)		100	300	—
(I C = 150 mAdc, V CE = 1.0 Vdc) (3)	MMBT2222	50	—	—
(I C = 500 mAdc, V CE = 10 Vdc) (3)	MMBT2222A	30	—	—
		40	—	—
Collector-Emitter Saturation Voltage(3)	$V_{CE(sat)}$			Vdc
(I C = 150 mAdc, I B = 15 mAdc)	MMBT2222	—	0.4	—
	MMBT2222A	—	0.3	—
(I C = 500mAdc, I B = 50 mAdc)	MMBT2222	—	1.6	—
	MMBT2222A	—	1.0	—
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			Vdc
(I C = 150 mAdc, I B = 15 mAdc)	MMBT2222	—	1.3	—
	MMBT2222A	0.6	1.2	—
(I C = 500 mAdc, I B = 50 mAdc)	MMBT2222	—	2.6	—
	MMBT2222A	—	2.0	—

SMALL-SIGNAL CHARACTERISTICS

Current-Gain — Bandwidth Product(4) (I C = 20mA, V CE= 20Vdc, f = 100MHz)	MMBT2222 MMBT2222A	f_T	250 300	—	MHz
Output Capacitance($V_{CB} = 10$ Vdc, $I_E = 0$, $f = 1.0$ MHz)	MMBT2222 MMBT2222A	C_{obo}	—	8.0 30	pF
Input Capacitance ($V_{EB} = 0.5$ Vdc, $I_C = 0$, $f = 1.0$ MHz)	MMBT2222 MMBT2222A	C_{ibo}	—	25 30	pF
Input Impedance($V_{CE} = 10$ Vdc, $I_C = 1.0$ mAdc, $f = 1.0$ kHz)	MMBT2222A MMBT2222A	h_{ie}	2.0 0.25	8.0 1.25	kΩ
Voltage Feedback Ratio($V_{CE}=10$ Vdc, $I_C=1.0$ mAdc, $f=1.0$ kHz)	MMBT2222A MMBT2222A	h_{re}	—	8.0 4.0	$\times 10^{-4}$
Small-Signal Current Gain($V_{CE}=10$ Vdc, $I_C=1.0$ mAdc, $f=1.0$ kHz)	MMBT2222A MMBT2222A	h_{fe}	50 75	300 375	—
Output Admittance($V_{CE}=10$ Vdc, $I_C = 1.0$ mAdc, $f = 1.0$ kHz)	MMBT2222A MMBT2222A	h_{oe}	5.0 25	35 200	μmhos
Current Base Time Constant ($V_{CB}= 20$ Vdc, $I_E = 20$ mAdc, $f = 31.8$ MHz)	MMBT2222A	r_b, C_C	—	150	ps
Noise Figure($V_{CE}=10$ Vdc, $I_C=100$ μAdc, $R_S=1.0$ kΩ, $f = 1.0$ kHz)	MMBT2222A	NF	—	4.0	dB

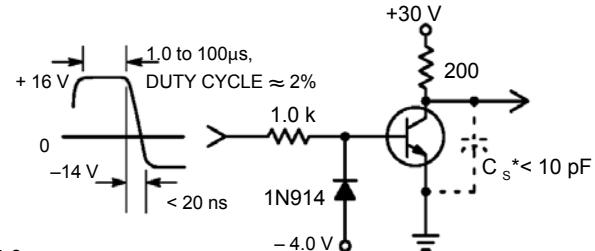
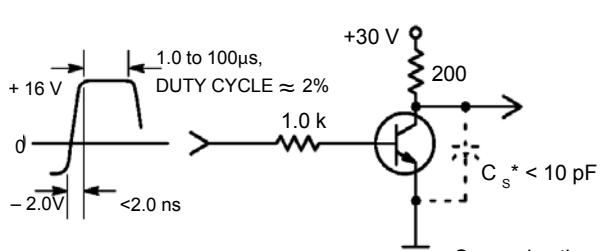
SWITCHING CHARACTERISTICS

Delay Time ($V_{CC} = 30$ Vdc, $V_{EB(off)} = -0.5$ Vdc)	t_d	—	10	ns
Rise Time ($I_C = 150$ mAdc, $I_{B1} = 15$ mAdc)	t_r	—	25	
Storage Time ($V_{CC} = 30$ Vdc, $I_C = 150$ mAdc)	t_s	—	225	ns
Fall Time ($I_{B1} = I_{B2} = 15$ mAdc)	t_f	—	60	

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle $\leq 2.0\%$.4. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

MMBT2222LT1 MMBT2222ALT1
S-MMBT2222LT1 S-MMBT2222ALT1

SWITCHING TIME EQUIVALENT TEST CIRCUITS



*Total shunt capacitance of test jig, connectors, and oscilloscope.

Figure 1. Turn-On Time

Figure 2. Turn-Off Time

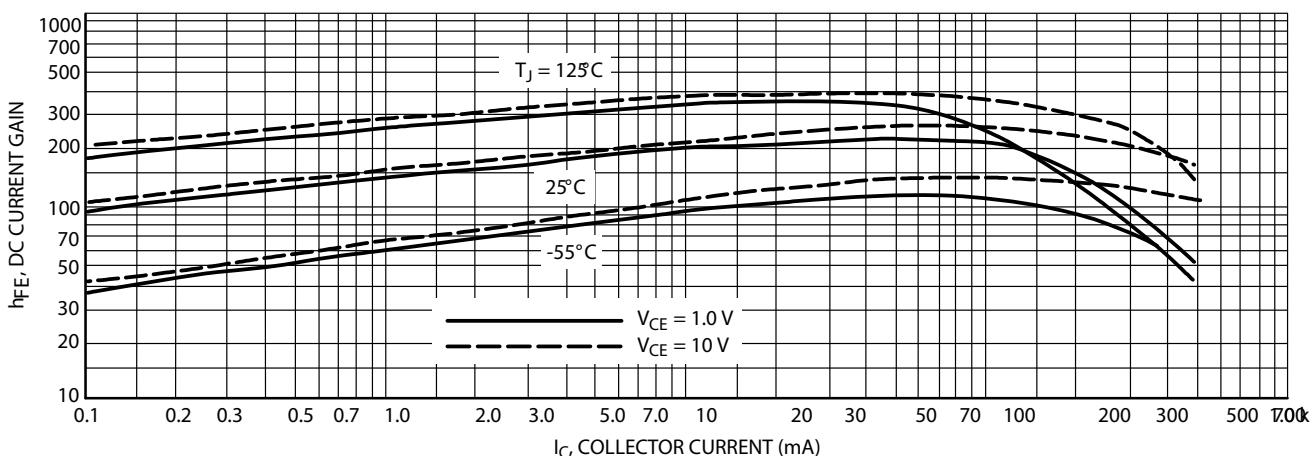


Figure 3. DC Current Gain

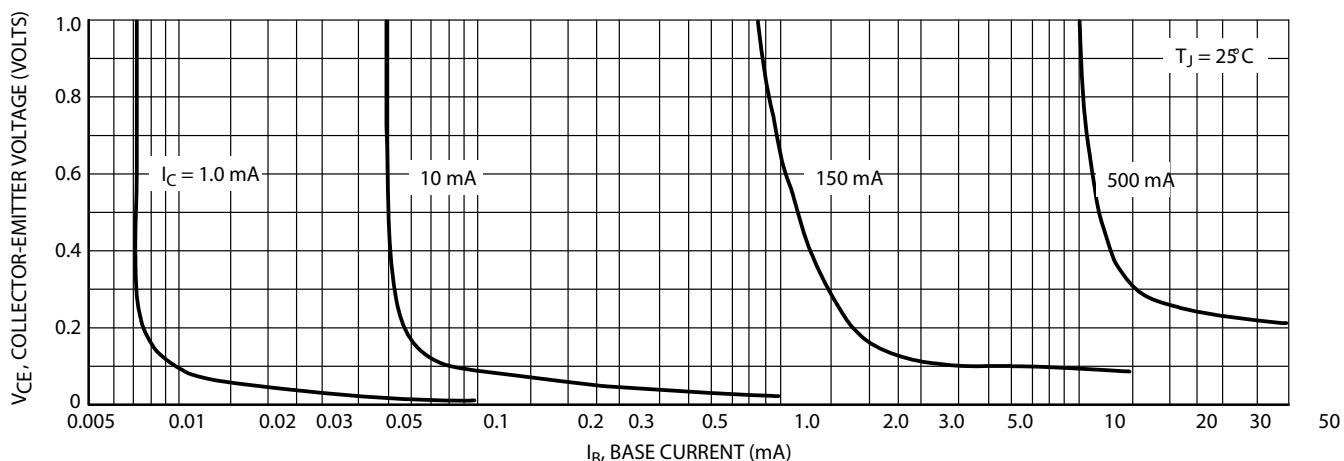


Figure 4. Collector Saturation Region

MMBT2222LT1 MMBT2222ALT1
S-MMBT2222LT1 S-MMBT2222ALT1

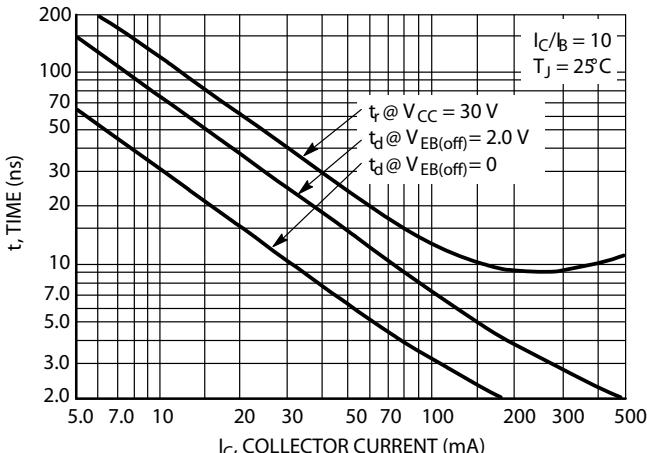


Figure 5. Turn-On Time

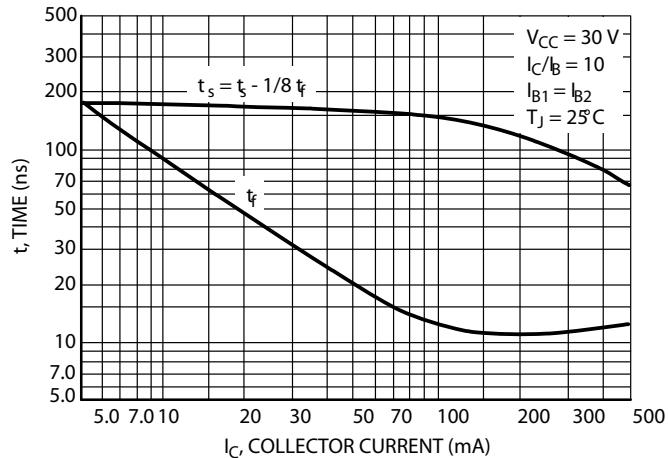


Figure 6. Turn-Off Time

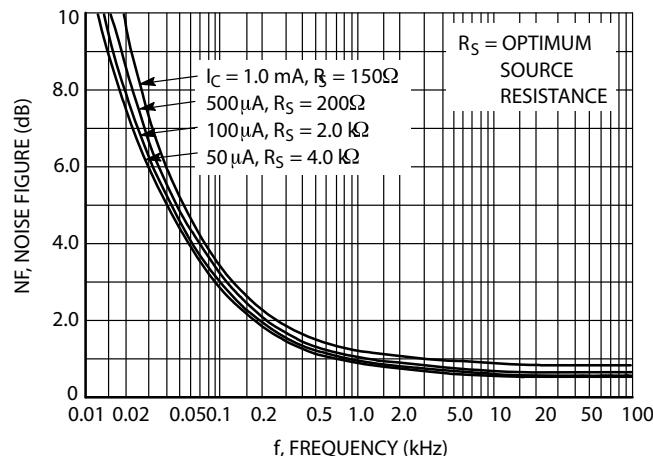


Figure 7. Frequency Effects

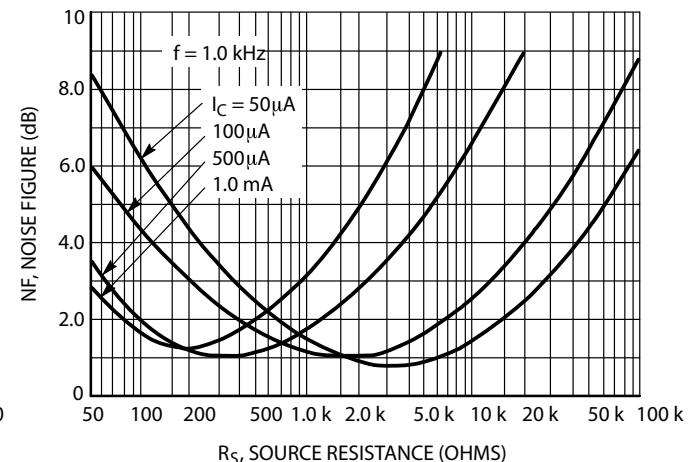


Figure 8. Source Resistance Effects

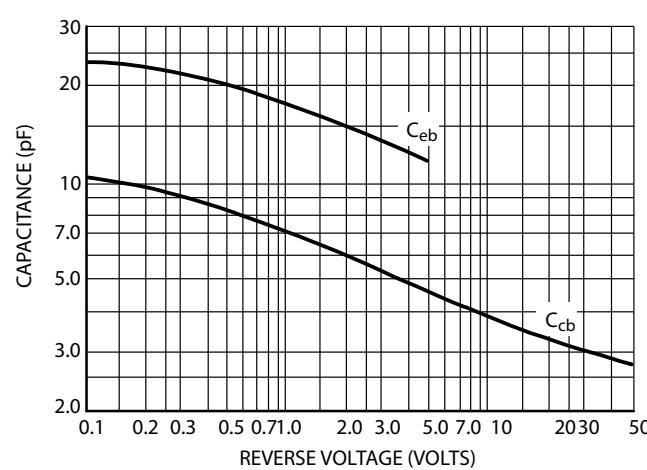


Figure 9. Capacitances

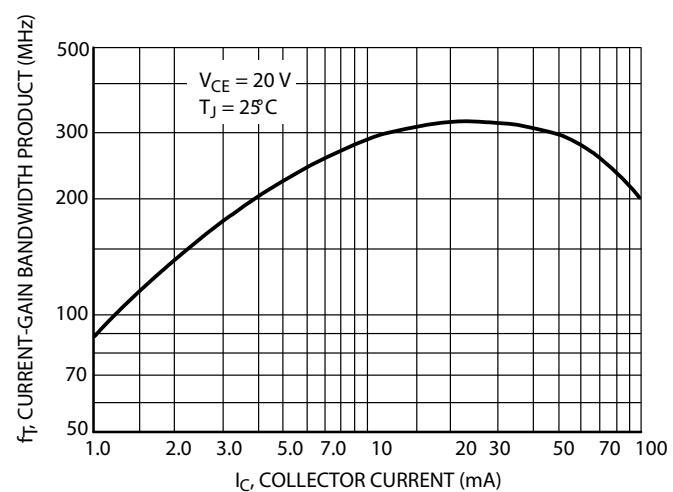


Figure 10. Current-Gain Bandwidth Product

MMBT2222LT1 MMBT2222ALT1
S-MMBT2222LT1 S-MMBT2222ALT1

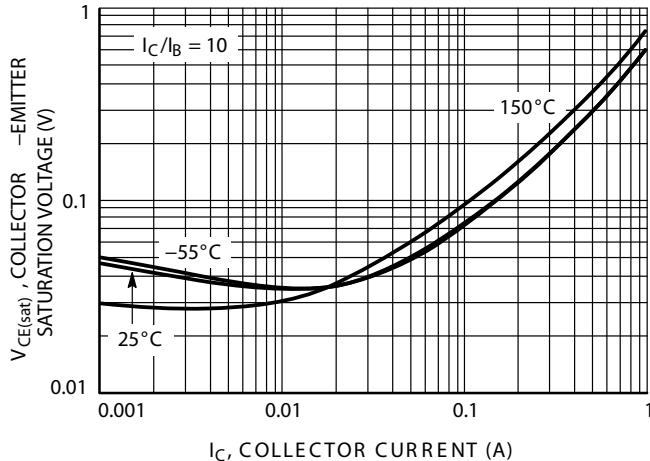


Figure 11. Collector Emitter Saturation Voltage vs. Collector Current

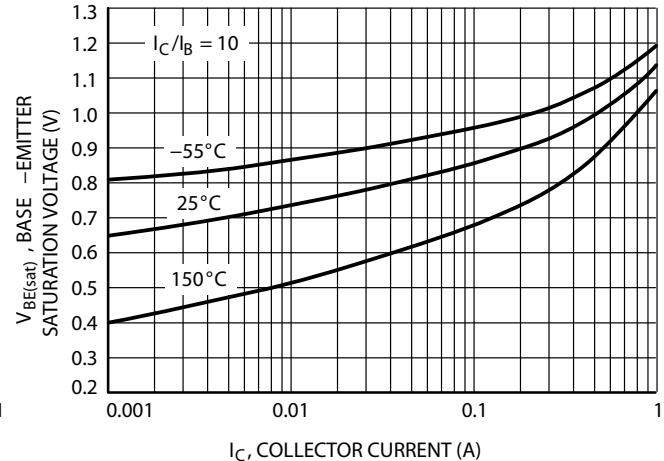


Figure 12. Base Emitter Saturation Voltage vs. Collector Current

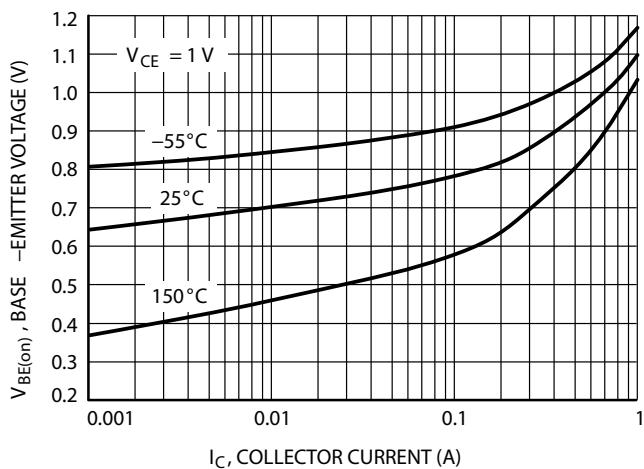


Figure 13. Base Emitter Voltage vs. Collector Current

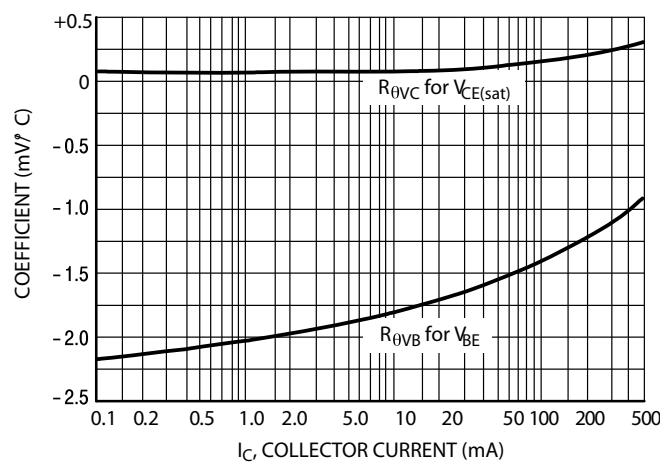


Figure 14. Temperature Coefficients

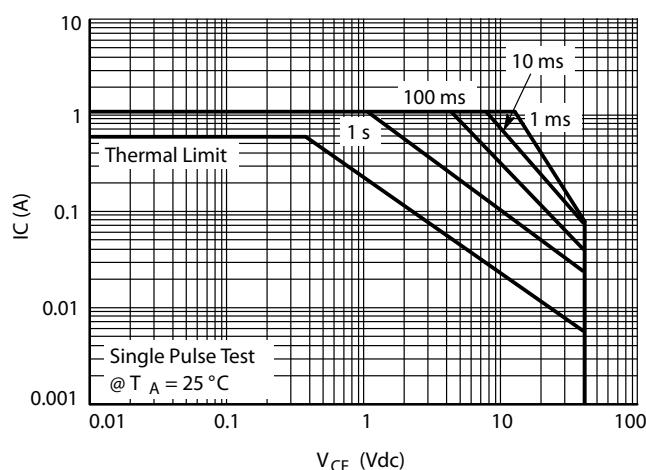


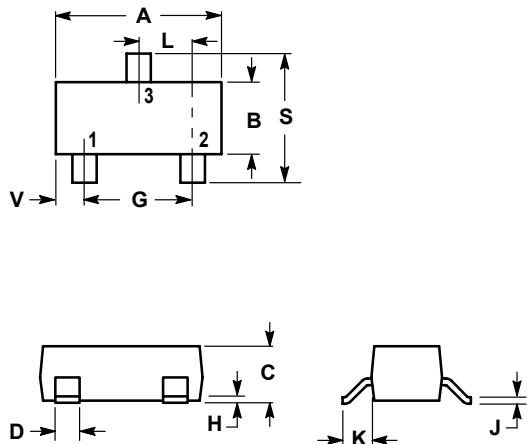
Figure 15. Safe Operating Area

MMBT2222LT1 MMBT2222ALT1
S-MMBT2222LT1 S-MMBT2222ALT1

SOT-23

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

